

# Characterization of thin irradiated epitaxial silicon sensors for the CMS phase II pixel upgrade

## The CMS experiment

**Large Hadron Collider:**

- Proton-proton collider
- 27 km circumference
- 4 interaction points

**Design parameters:**

- CM energy = 14 TeV
- Bunch spacing = 25 ns
- Luminosity =  $10^{34} \text{ cm}^{-2} \text{ s}^{-1}$

**Achievements:**

- SM tests
- BSM searches
- Discovery of the Higgs boson

**Compact Muon Solenoid:**

- General purpose detector
- Cylindrical symmetry

## The phase II pixel upgrade

**2023: High-Luminosity LHC**

- Luminosity of  $5 \times 10^{34} \text{ cm}^{-2} \text{ s}^{-1}$
- Replacement of the tracker

**Outer tracker:**

- Momentum information for L1 trigger
- 2-strip and pixel-strip modules

**Pixel modules:**

- Hybrid configuration
- Pixel area =  $2500 \mu\text{m}^2$
- $\sim 5 \text{ m}^2$  of pixel sensors

**Radiation tolerance**

For the innermost pixel layer, after  $3000 \text{ fb}^{-1}$

- $\Phi_{\text{eq}} \approx 10^{16} \text{ cm}^{-2}$
- Dose = 5 MGy
- Hit rate = 1-2 GHz  $\text{cm}^{-2}$

Several materials and configurations under study

## Sensors under study

**Thin planar sensors** (black) compared to thicker ones (300  $\mu\text{m}$ , red and green)

- Before irradiation: smaller signal
- After irradiation: weaker degradation

**Diodes and strip detectors:**

- High resistivity epitaxial silicon
- n- and p-bulk
- Active thickness = 100  $\mu\text{m}$
- Total thickness = 330  $\mu\text{m}$
- Max  $\Phi_{\text{eq}} = 1.3 \times 10^{16} \text{ cm}^{-2}$
- 800 MeV and 23 GeV protons
- No annealing

Strip detector with p-stop insulation, pitch = 80  $\mu\text{m}$

## Test beam setup

- DESY  $e^+e^-$  beam
- AIDA beam telescope
- 4 trigger scintillators
- Sensor housing
- Moving stage
- Cooling for irradiated sensors

**ALiBaVa readout system**

- Based on LHCb readout chip
- Readout of positive and negative signals
- Analog information

3-5 GeV  $e^+e^-$

## Noise

**Noise dominated by readout electronics and sensor capacitance for bias < 800 V**

**Single channel noise**

**Mean noise amplitude**

4 ADC  $\approx 700 e^-$

## Charge Collection Efficiency

Charge definition based on telescope tracks:

- Charge := sum of the signal over 5 strips, centered on the telescope prediction
- No threshold applied
- Fake rejection

**Charge distribution fit:**

- Gauss function constrained to the noise
- Landau-Gauss convolution

**CCE of n-in-p strip sensors 90% after  $\Phi_{\text{eq}} = 3 \times 10^{15} \text{ cm}^{-2}$**

- Diodes show better CCE than strip sensors
- Charge multiplication is present in diodes, to be investigated in strip detectors

**CCE of strip detectors from test beam:**

- Landau MPV from fit
- Normalization using non-irradiated sensors in range 200-400 V
- Only statistical errors taken into account

**CCE of diodes using TCT:**

- p-bulk, p-spray
- Infrared laser
- Normalization using non-irradiated sensors
- T = 0  $^\circ\text{C}$  (open symbols) and -20  $^\circ\text{C}$  (full)

## Detection efficiency estimation

**The irradiation produces a smearing of the distribution (charge sharing)**

Signal distribution of the seed strip

## Seed threshold to have 95% efficiency

10 ADC  $\approx 1800 e^-$

## Conclusions & Outlook

- The CCE of thin epitaxial silicon diodes and strip sensors has been measured
- Thin epitaxial silicon is a promising material for the CMS pixel phase II upgrade
- Extend the test beam analysis to different sensors and higher fluences
- Choice of material and thickness: end of 2016
- Prototype test sensors in 2017

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